

2N4125



PNP General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents of 10 μA to 100 mA.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	30	V
Vcbo	Collector-Base Voltage	30	V
V _{EBO}	Emitter-Base Voltage	4.0	V
lc	Collector Current - Continuous	200	mA
TJ, Tstg	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES: 1) These ratings are based on a maximum junction temperature of 150 degrees C. 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах	Units
		2N4125	
P _D	Total Device Dissipation	625	mW
	Derate above 25°C	5.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W
$R_{\theta_{JA}}$	Thermal Resistance, Junction to Ambient	200	°C/W

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Symbol	Parameter	Test Conditions	Min	Max	Units
	DAGTERIOTION				
	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 1.0$ mA, $I_{\rm B} = 0$	30		V
/ _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{C} = 10 \ \mu A, I_{E} = 0$	30		V
/(BR)EBO	Emitter-Base Breakdown Voltage	$I_{E} = 10 \ \mu A, I_{C} = 0$	4.0		V
СВО	Collector-Cutoff Current	$V_{CB} = 20 \text{ V}, I_E = 0$		50	nA
EBO	Emitter-Cutoff Current	$V_{EB} = 3.0 \text{ V}, \text{ Ic} = 0$		50	nA
N _{FE}	DC Current Gain	$V_{CE} = 1.0 \text{ V}, I_C = 2.0 \text{ mA}$ $V_{CE} = 1.0 \text{ V}, I_C = 50 \text{ mA}$	50 25	150	V
ĴFE	DC Current Gain			150	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA}$		0.4	V
/	Base-Emitter Saturation Voltage	$I_{\rm C} = 50 \text{ mA}, I_{\rm B} = 5.0 \text{ mA}$		0.95	V
V _{BE(sat)}	, , , , , , , , , , , , , , , , , , ,				
SMALL S	IGNAL CHARACTERISTICS Output Capacitance	V _{CB} = 5.0 V, f = 100 kHz		4.5	pF
SMALL S Cod	IGNAL CHARACTERISTICS Output Capacitance Input Capacitance	V _{BE} = 0.5 V, f = 100 kHz		4.5 10	pF pF
	IGNAL CHARACTERISTICS Output Capacitance		50		

PNP General Purpose Amplifier (continued) **Typical Characteristics** Typical Pulsed Current Gain **Collector-Emitter Saturation** V_{CBA1} - COLLECTOR EMITTER VOLTAGE (V) 0.2 0.0 0 0 0 0 0 0 0 Voltage vs Collector Current vs Collector Current V_{CE} = 1.0V β = 10 ÷ 125 125°C 40 °C - 40 °C 200 10 100 20 0.2 0.5 1 2 5 10 50 100 1 Ic-COLLECTOR CURRENT (mA) Ic - COLLECTOR CURRENT (mA) **Base-Emitter Saturation** Base Emitter ON Voltage vs **Collector Current** Voltage vs Collector Current ß = 10 40 °C -----40 °C 25 ċ 25 125 °C $V_{CE} = 1V$ 0 L 10 I_c- COLLECTOR CURRENT (mA) 200 100 1 1 I_c-COLLECTOR CURRENT (mA) 25 10 **Collector-Cutoff Current Common-Base Open Circuit** vs Ambient Temperature **Input and Output Capacitance** vs Reverse Bias Voltage

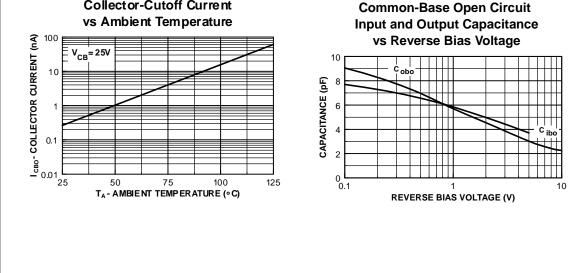
NF 250

hre- **TYPICAL PULSED CURRENT** 00 00 00 01 00 05

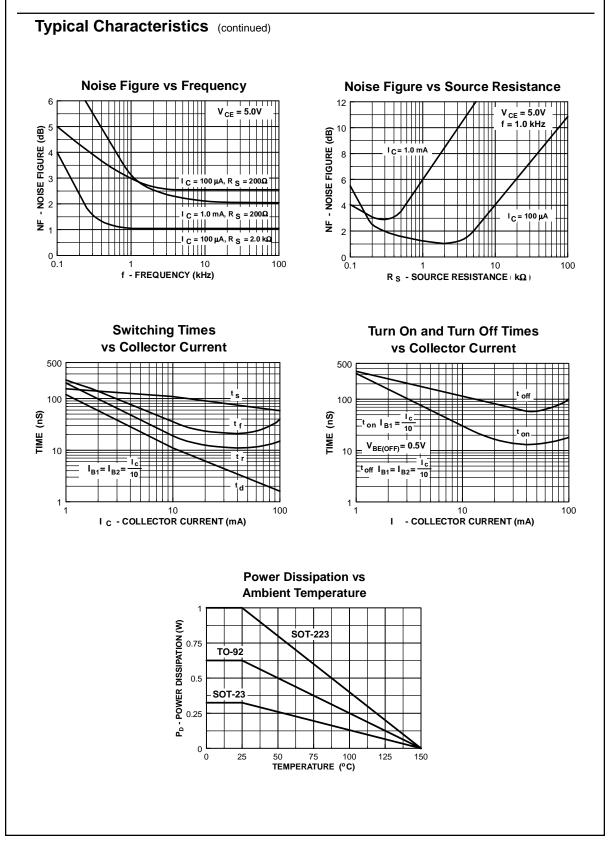
Å 0.2

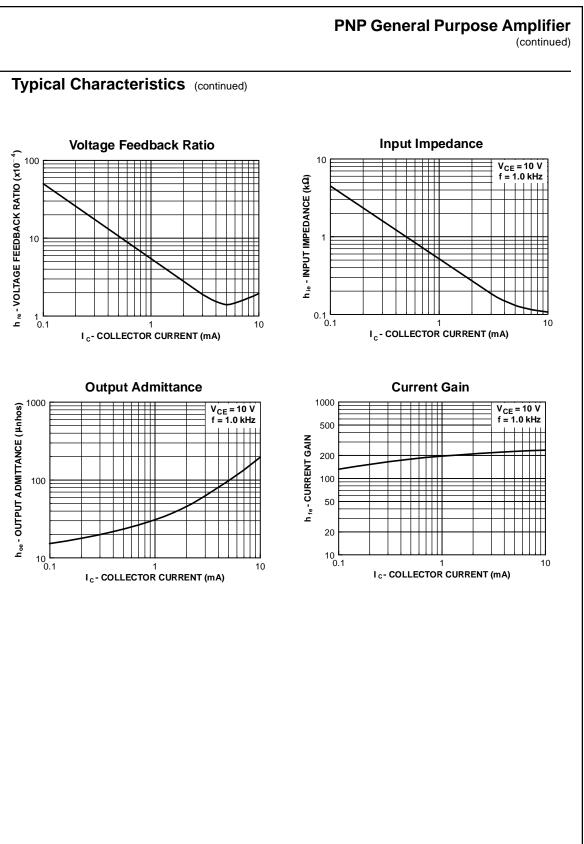
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50 L 0.1



PNP General Purpose Amplifier (continued)





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